



128K x 16 Static RAM

Features

- Low voltage range:
 - CY62137BV18: 1.75V–1.95V
- Ultra-low active, standby power
- Easy memory expansion with \overline{CE} and \overline{OE} features
- TTL-compatible inputs and outputs
- Automatic power-down when deselected
- CMOS for optimum speed/power

Functional Description

The CY62137BV18 is a high-performance CMOS static RAM organized as 131,072 words by 16 bits. This device features advanced circuit design to provide ultra-low active current. This is ideal for providing More Battery Life™ (MoBL™) in portable applications such as cellular telephones. The device also has an automatic power-down feature that significantly reduces power consumption by 99% when addresses are not toggling. The device can also be put into standby mode when deselected (\overline{CE} HIGH) or when \overline{CE} is LOW and both \overline{BLE} and

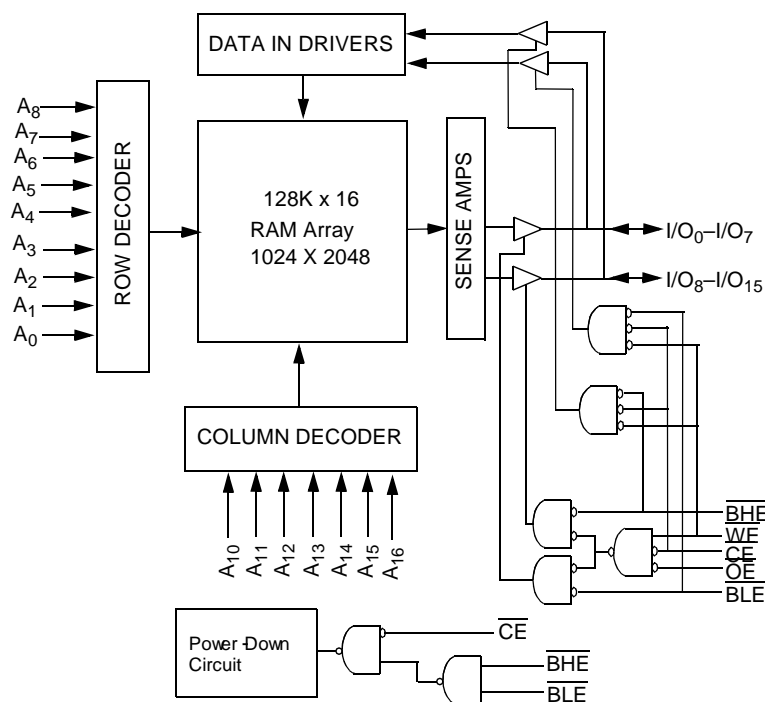
\overline{BHE} are HIGH. The input/output pins (I/O_0 through I/O_{15}) are placed in a high-impedance state when: deselected (\overline{CE} HIGH), outputs are disabled (\overline{OE} HIGH), \overline{BHE} and \overline{BLE} are disabled (\overline{BHE} , \overline{BLE} HIGH), or during a write operation (\overline{CE} LOW, and \overline{WE} LOW).

Writing to the device is accomplished by taking Chip Enable (\overline{CE}) and Write Enable (\overline{WE}) inputs LOW. If Byte Low Enable (\overline{BLE}) is LOW, then data from I/O pins (I/O_0 through I/O_7), is written into the location specified on the address pins (A_0 through A_{16}). If Byte High Enable (\overline{BHE}) is LOW, then data from I/O pins (I/O_8 through I/O_{15}) is written into the location specified on the address pins (A_0 through A_{16}).

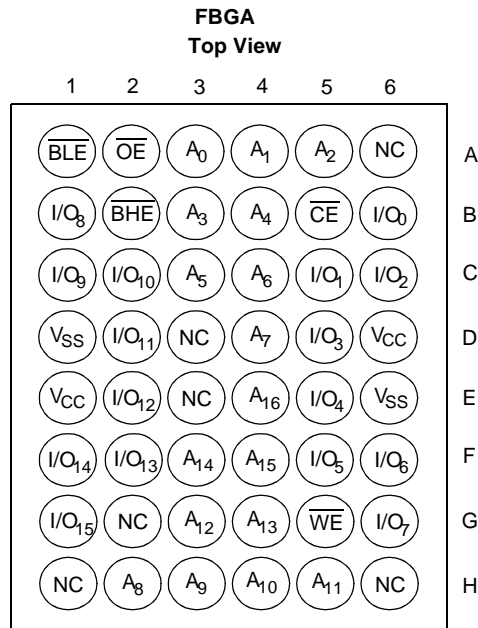
Reading from the device is accomplished by taking Chip Enable (\overline{CE}) and Output Enable (\overline{OE}) LOW while forcing the Write Enable (\overline{WE}) HIGH. If Byte Low Enable (\overline{BLE}) is LOW, then data from the memory location specified by the address pins will appear on I/O_0 to I/O_7 . If Byte High Enable (\overline{BHE}) is LOW, then data from memory will appear on I/O_8 to I/O_{15} . See the Truth Table at the back of this data sheet for a complete description of read and write modes.

The CY62137BV18 is available in 48-ball FBGA packaging.

Logic Block Diagram



Pin Configuration



Maximum Ratings

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature	-65°C to +150°C
Ambient Temperature with Power Applied.....	-55°C to +125°C
Supply Voltage to Ground Potential	-0.5V to +2.4V

DC Voltage Applied to Outputs

in High Z State ^[1]	-0.5V to V _{CC} + 0.5V
DC Input Voltage ^[1]	-0.5V to V _{CC} + 0.5V
Output Current into Outputs (LOW).....	20 mA
Static Discharge Voltage	>2001V (per MIL-STD-883, Method 3015)
Latch-Up Current.....	>200 mA

Operating Range

Device	Range	Ambient Temperature	V _{CC}
CY62137BV18	Industrial	-40°C to +85°C	1.75V to 1.95V

Product Portfolio

Product	V _{CC} Range			Power	Power Dissipation (Industrial)			
					Operating (I _{CC})		Standby (I _{SB2})	
	V _{CC(min)}	V _{CC(typ)} ^[2]	V _{CC(max)}		Typ. ^[2]	Max.	Typ. ^[2]	Max
CY62137BV18	1.75V	1.80V	1.95V	LL	3 mA	7 mA	1 μA	15 μA

Notes:

- V_{IL(min.)} = -2.0V for pulse durations less than 20 ns.
- Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at V_{CC} = V_{CC Typ}, T_A = 25°C.

Electrical Characteristics Over the Operating Range

Parameter	Description	Test Conditions			CY62137BV18			Unit
					Min.	Typ. ^[2]	Max.	
V _{OH}	Output HIGH Voltage	I _{OH} = -0.1 mA	V _{CC} = 1.75V	1.5			V	
V _{OL}	Output LOW Voltage	I _{OL} = 0.1 mA	V _{CC} = 1.75V			0.2	V	
V _{IH}	Input HIGH Voltage		V _{CC} = 1.95V	1.4		V _{CC} + 0.3V	V	
V _{IL}	Input LOW Voltage		V _{CC} = 1.75V	-0.5		0.4	V	
I _{IX}	Input Load Current	GND ≤ V _I ≤ V _{CC}			-1	±1	+1	μA
I _{OZ}	Output Leakage Current	GND ≤ V _O ≤ V _{CC} , Output Disabled			-1	+1	+1	μA
I _{CC}	V _{CC} Operating Supply Current	I _{OUT} = 0 mA, f = f _{MAX} = 1/t _{RC} , CMOS levels	V _{CC} = 1.95V		3	7	mA	
		I _{OUT} = 0 mA, f = 1 MHz, CMOS Levels			1	2	mA	
I _{SB1}	Automatic CE Power-Down Current—CMOS Inputs	$\overline{CE} \geq V_{CC} - 0.3V$, $V_{IN} \geq V_{CC} - 0.3V$ or $V_{IN} \leq 0.3V$, f = f _{MAX} (Address and Data Only), f=0 (OE, WE, BHE, and BLE)					100	μA
I _{SB2}	Automatic CE Power-Down Current—CMOS Inputs	$\overline{CE} \geq V_{CC} - 0.3V$ $V_{IN} \geq V_{CC} - 0.3V$ or $V_{IN} \leq 0.3V$, f = 0	V _{CC} = 1.95V	LL		1	15	μA

Capacitance^[3]

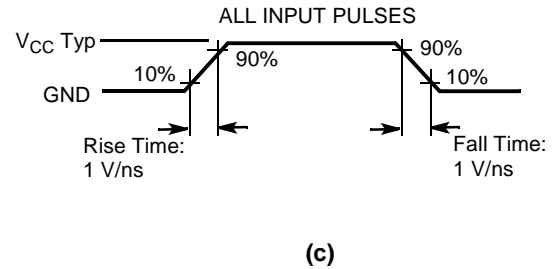
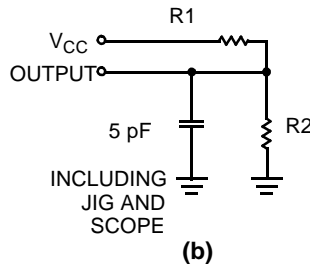
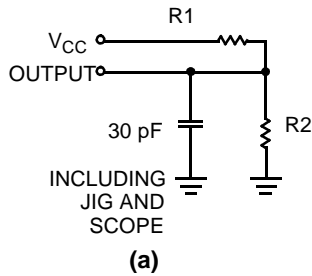
Parameter	Description	Test Conditions	Max.	Unit
C _{IN}	Input Capacitance	T _A = 25°C, f = 1 MHz, V _{CC} = V _{CC} (typ.)	6	pF
C _{OUT}	Output Capacitance		8	pF

Thermal Resistance

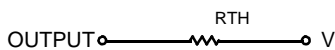
Description	Test Conditions	Symbol	BGA	Unit
Thermal Resistance (Junction to Ambient) ^[3]	Still Air, soldered on a 4.25 x 1.125 inch, 4-layer printed circuit board	θ _{JA}	55	°C/W
Thermal Resistance (Junction to Case) ^[3]		θ _{JC}	16	°C/W

Note:

- Tested initially and after any design or process changes that may affect these parameters.

AC Test Loads and Waveforms


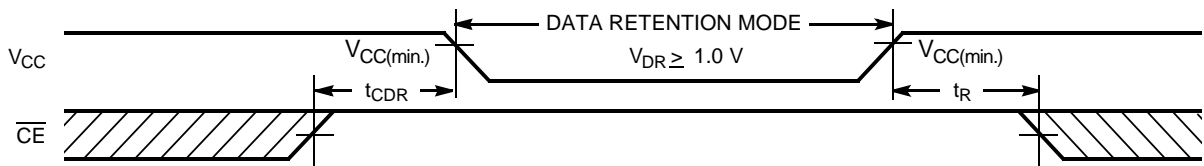
Equivalent to: THÉVENIN EQUIVALENT



Parameters	1.8V	Unit
R1	15294	Ohms
R2	11300	Ohms
R _{TH}	6500	Ohms
V _{TH}	0.85	Volts

Data Retention Characteristics (Over the Operating Range)

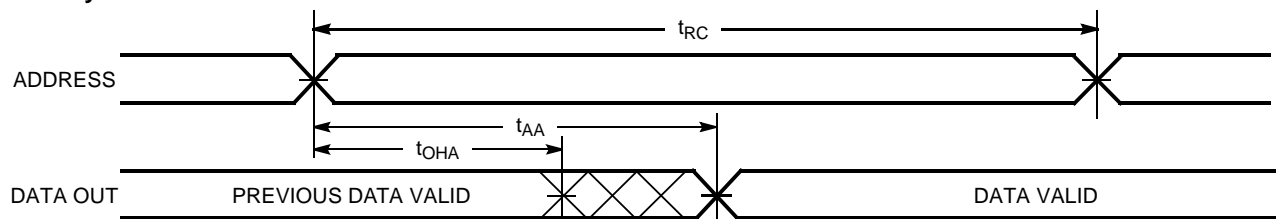
Parameter	Description	Conditions ^[5]	Min.	Typ. ^[2]	Max.	Unit
V _{DR}	V _{CC} for Data Retention		1.0		1.95	V
I _{CCDR}	Data Retention Current	V _{CC} = 1.0V CE ≥ V _{CC} - 0.3V, V _{IN} ≥ V _{CC} - 0.3V or V _{IN} ≤ 0.3V No input may exceed V _{CC} +0.3V	LL	1	7.5	μA
t _{CDR} ^[3]	Chip Deselect to Data Retention Time		0			ns
t _R ^[4]	Operation Recovery Time		100			μs

Data Retention Waveform

Notes:

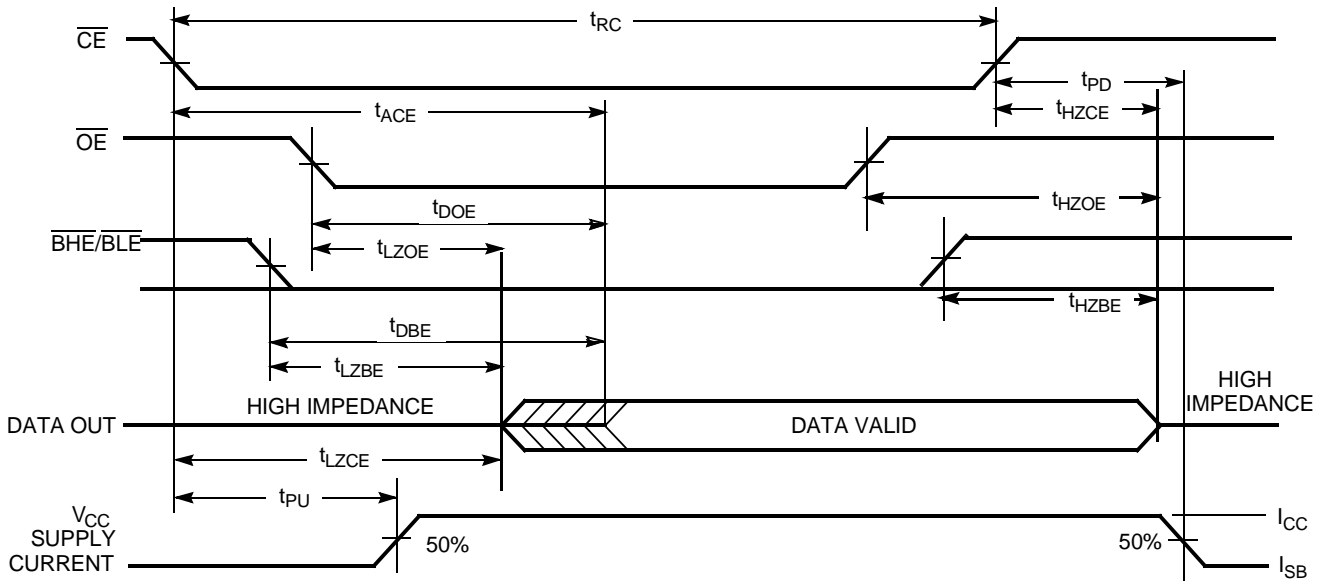
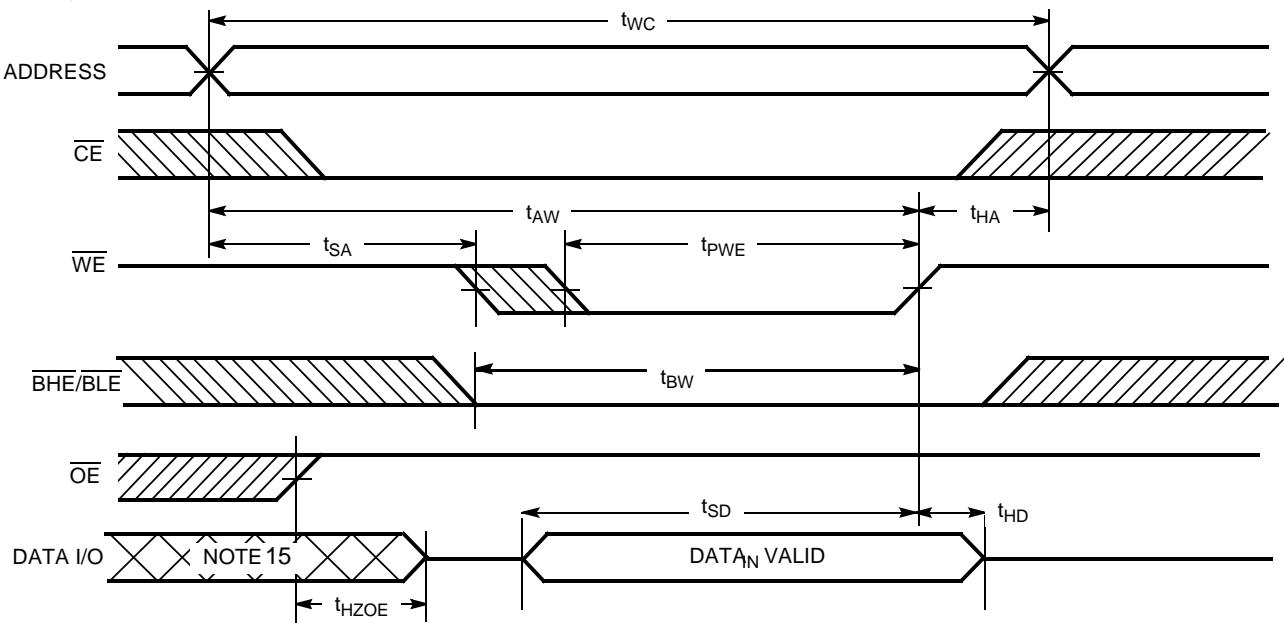
- Full device operation requires linear V_{CC} ramp from V_{DR} to V_{CC(min.)} ≥ 100 μs or stable at V_{CC(min.)} ≥ 100 μs.
- Test conditions assume signal transition time of 5 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to V_{CC} typ., and output loading of the specified I_{OL}/I_{OH} and 30 pF load capacitance.

Switching Characteristics Over the Operating Range^[5]

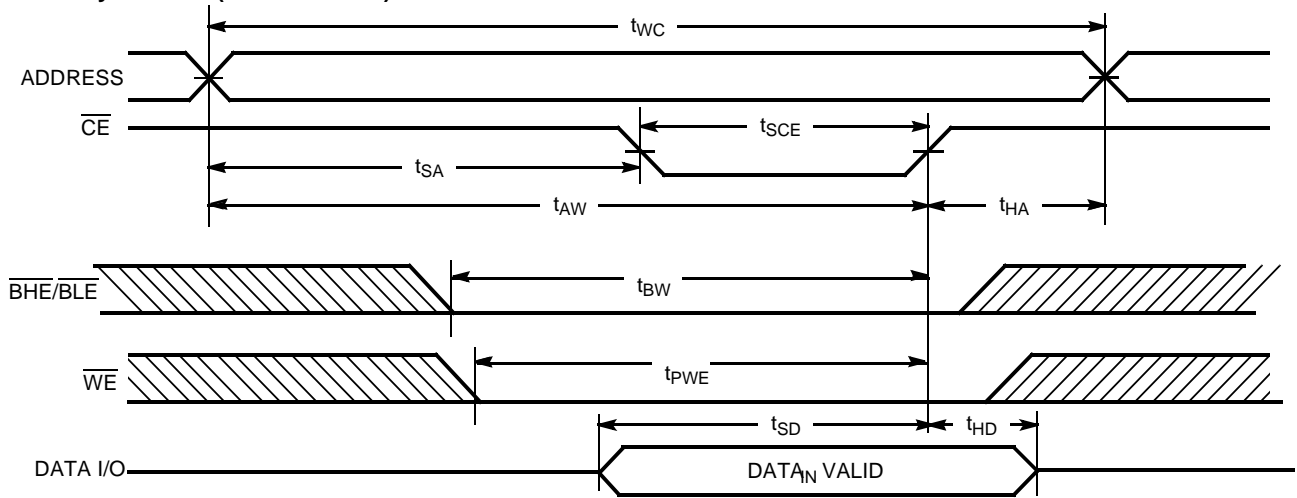
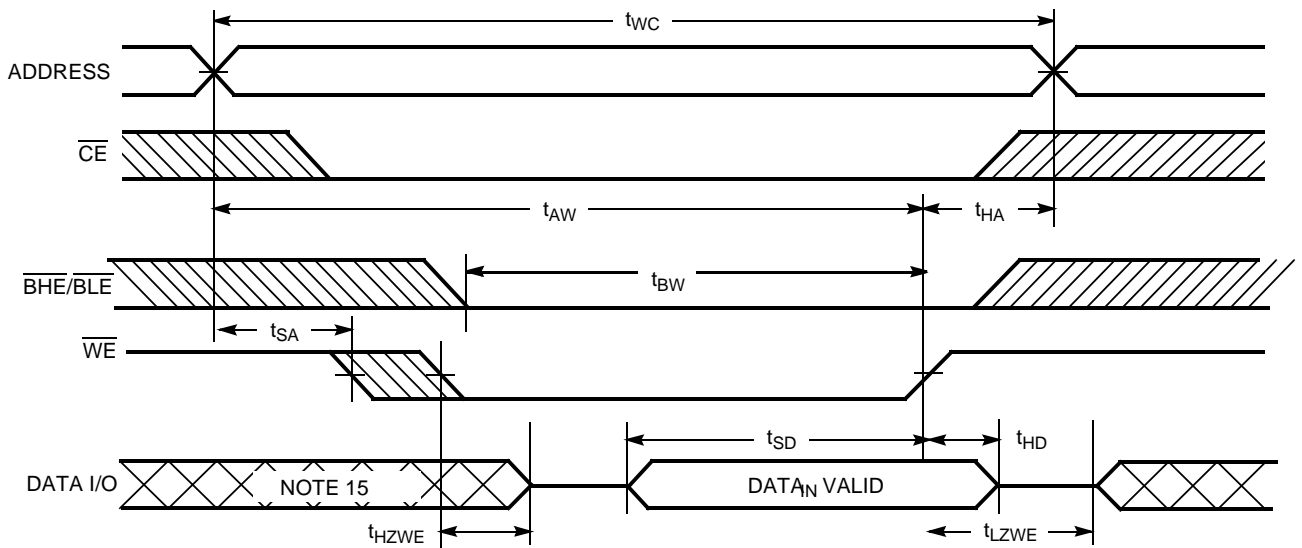
Parameter	Description	70 ns		Unit
		Min.	Max.	
READ CYCLE				
t_{RC}	Read Cycle Time	70		ns
t_{AA}	Address to Data Valid		70	ns
t_{OHA}	Data Hold from Address Change	10		ns
t_{ACE}	\overline{CE} LOW to Data Valid		70	ns
t_{DOE}	\overline{OE} LOW to Data Valid		35	ns
t_{LZOE}	\overline{OE} LOW to Low Z ^[6]	5		ns
t_{HZOE}	\overline{OE} HIGH to High Z ^[6, 7]		25	ns
t_{LZCE}	\overline{CE} LOW to Low Z ^[6]	10		ns
t_{HZCE}	\overline{CE} HIGH to High Z ^[6, 7]		25	ns
t_{PU}	\overline{CE} LOW to Power-Up	0		ns
t_{PD}	\overline{CE} HIGH to Power-Down		70	ns
t_{DBE}	$\overline{BLE} / \overline{BHE}$ LOW to Data Valid		35	ns
t_{LZBE}	$\overline{BLE} / \overline{BHE}$ LOW to Low Z ^[6, 7]	5		ns
t_{HZBE}	$\overline{BLE} / \overline{BHE}$ HIGH to High Z ^[8]		25	ns
WRITE CYCLE^[8, 9]				
t_{WC}	Write Cycle Time	70		ns
t_{SCE}	\overline{CE} LOW to Write End	60		ns
t_{AW}	Address Set-Up to Write End	60		ns
t_{HA}	Address Hold from Write End	0		ns
t_{SA}	Address Set-Up to Write Start	0		ns
t_{PWE}	\overline{WE} Pulse Width	50		ns
t_{BW}	$\overline{BLE} / \overline{BHE}$ LOW to Write End	60		ns
t_{SD}	Data Set-Up to Write End	30		ns
t_{HD}	Data Hold from Write End	0		ns
t_{HZWE}	\overline{WE} LOW to High Z ^[6, 7]		25	ns
t_{LZWE}	\overline{WE} HIGH to Low Z ^[6]	10		ns

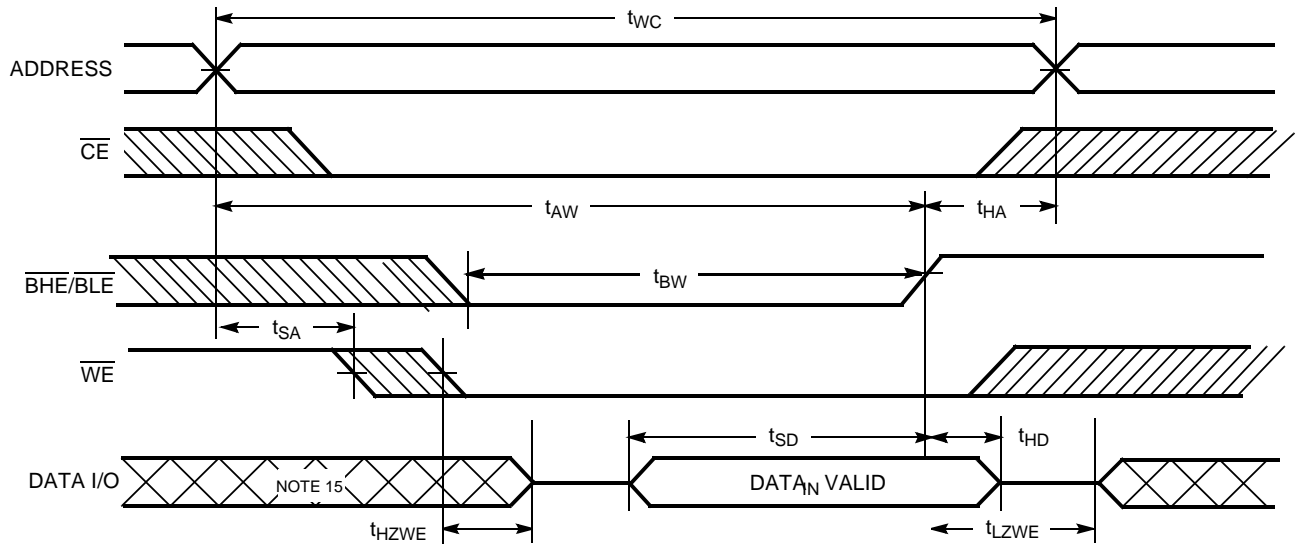
Switching Waveforms
Read Cycle No. 1^[10, 11]

Notes:

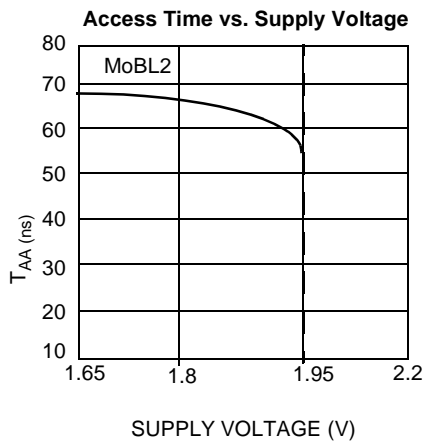
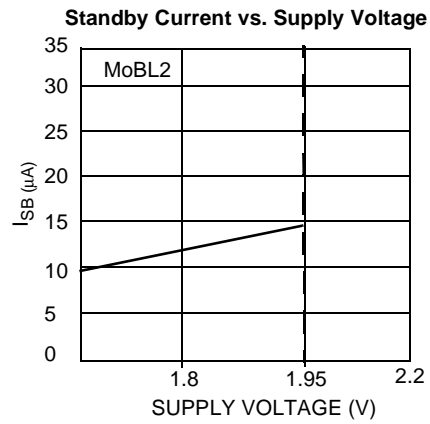
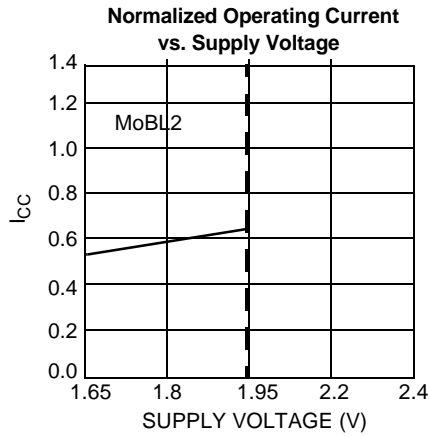
6. At any given temperature and voltage condition, t_{HZCE} is less than t_{LZCE} , t_{HZOE} is less than t_{LZOE} , and t_{HZWE} is less than t_{LZWE} for any given device.
7. t_{HZOE} , t_{HZCE} , and t_{HZWE} are specified with $C_L = 5$ pF as in part (b) of AC Test Loads. Transition is measured ± 500 mV from steady-state voltage.
8. The internal write time of the memory is defined by the overlap of \overline{CE} LOW and \overline{WE} LOW. Both signals must be LOW to initiate a write and either signal can terminate a write by going HIGH. The data input set-up and hold timing should be referenced to the rising edge of the signal that terminates the write.
9. The minimum write cycle time for write cycle #3 (\overline{WE} controlled, \overline{OE} LOW) is the sum of t_{HZWE} and t_{SD} .
10. Device is continuously selected. \overline{OE} , $\overline{CE} = V_{IL}$.
11. \overline{WE} is HIGH for read cycle.

Switching Waveforms (continued)
Read Cycle No. 2 [11, 12]

Write Cycle No. 1 (WE Controlled) [8, 13, 14]

Notes:

12. Address valid prior to or coincident with \overline{CE} transition LOW.
13. Data I/O is high impedance if $OE = V_{IH}$.
14. If \overline{CE} goes HIGH simultaneously with WE HIGH, the output remains in a high-impedance state.
15. During this period, the I/Os are in output state and input signals should not be applied.

Switching Waveforms (continued)
Write Cycle No. 2 ($\overline{\text{CE}}$ Controlled)^[8, 13, 14]

Write Cycle No. 3 ($\overline{\text{WE}}$ Controlled, $\overline{\text{OE}}$ LOW)^[9, 14]


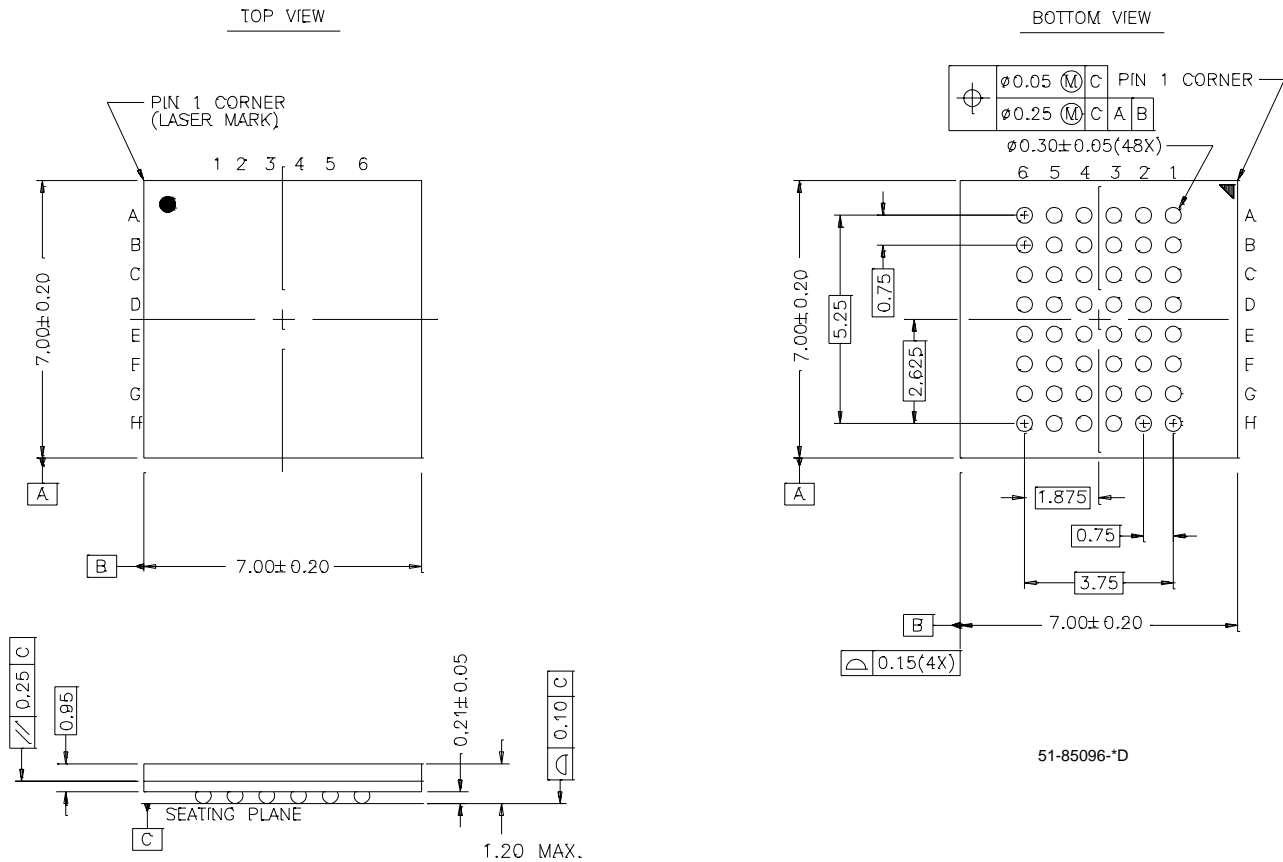
Switching Waveforms (continued)
Write Cycle No. 4 ($\overline{\text{BHE}}/\overline{\text{BLE}}$ Controlled, $\overline{\text{OE}}$ LOW)^[15]


Typical DC and AC Characteristics

Truth Table

CE	WE	OE	BHE	BLE	Inputs/Outputs	Mode	Power
H	X	X	X	X	High Z	Deselect/Power-Down	Standby (I_{SB})
L	X	X	H	H	High Z	Deselect/Power-Down	Standby (I_{SB})
L	H	L	L	L	Data Out (I/O ₀ –I/O ₁₅)	Read	Active (I_{CC})
L	H	L	H	L	Data Out (I/O ₀ –I/O ₇); I/O ₈ –I/O ₁₅ in High Z	Read	Active (I_{CC})
L	H	L	L	H	Data Out (I/O ₈ –I/O ₁₅); I/O ₀ –I/O ₇ in High Z	Read	Active (I_{CC})
L	H	H	L	L	High Z	Deselect/Output Disabled	Active (I_{CC})
L	H	H	H	L	High Z	Deselect/Output Disabled	Active (I_{CC})
L	H	H	L	H	High Z	Deselect/Output Disabled	Active (I_{CC})
L	L	X	L	L	Data In (I/O ₀ –I/O ₁₅)	Write	Active (I_{CC})
L	L	X	H	L	Data In (I/O ₀ –I/O ₇); I/O ₈ –I/O ₁₅ in High Z	Write	Active (I_{CC})
L	L	X	L	H	Data In (I/O ₈ –I/O ₁₅); I/O ₀ –I/O ₇ in High Z	Write	Active (I_{CC})

Ordering Information

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
70	CY62137BV18LL-70BAI	BA48A	48-Ball Fine Pitch BGA	Industrial

Package Diagrams
48-Ball (7.00 mm x 7.00 mm x 1.2 mm) FBGA BA48A




Document Title: CY62137VB MoBL2™ 128K x 16 Static RAM Document Number: 38-05239				
REV.	ECN NO.	Issue Date	Orig. of Change	Description of Change
**	114803	04/11/02	DSG	Change from Spec number: 38-01051 to 38-05293